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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/724,201	12/01/2003	Chi-Wen Liu	0941-0872P 8748	
2292	7590 03/07/2006		EXAMINER	
	EWART KOLASCH &	PHAM, THANHHA S		
PO BOX 74 FALLS CH	/ URCH, VA 22040-0747	7	ART UNIT PAPER NUMBER	
	,		2813	
			DATE MAILED: 03/07/2006	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Applica	ation No.	Applicant(s)	
	10/724	,201	LIU ET AL.	
Office Action Summary	Examir	ner	Art Unit	
	Thanhh	a Pham	2813	
The MAILING DATE of this comp	nunication appears on	the cover sheet with the	correspondence address	
A SHORTENED STATUTORY PERIOTHE MAILING DATE OF THIS COMM - Extensions of time may be available under the proviafter SIX (6) MONTHS from the mailing date of this - If the period for reply specified above is less than th - If NO period for reply is specified above, the maxim - Failure to reply within the set or extended period for Any reply received by the Office later than three mo earned patent term adjustment. See 37 CFR 1.704	UNICATION. sions of 37 CFR 1.136(a). In no communication. irty (30) days, a reply within the si um statutory period will apply and reply will, by statute, cause the si nths after the mailing date of this	event, however, may a reply be til statutory minimum of thirty (30) day d will expire SIX (6) MONTHS from application to become ABANDONE	mely filed ys will be considered timely. In the mailing date of this communication. In (35 U.S.C. § 133).	
Status				
 Responsive to communication(s This action is FINAL. Since this application is in condiction closed in accordance with the present the	2b)☐ This action is tion for allowance exce	s non-final. ept for formal matters, pr		
Disposition of Claims				
4) ⊠ Claim(s) 1-21 is/are pending in the day Of the above claim(s) 1-14 is 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) 15-21 is/are rejected. 7) □ Claim(s) is/are objected to result and subject to	/are withdrawn from co			
9)☐ The specification is objected to b	v the Evaminer			
10) ☐ The drawing(s) filed on <u>01 Decentle</u> Applicant may not request that any Replacement drawing sheet(s) including The oath or declaration is object	mber 2003 is/are: a)⊠objection to the drawing(solding the correction is req	s) be held in abeyance. Se uired if the drawing(s) is ob	e 37 CFR 1.85(a). ojected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119				
12) Acknowledgment is made of a cl a) All b) Some * c) None of the prior of the prior of the prior of the certified copies of the prior of the certified copies of the certifi	of: prity documents have b prity documents have b pies of the priority docu national Bureau (PCT F	een received. een received in Applicat ments have been receiv Rule 17.2(a)).	ion No ed in this National Stage	
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Revi		4) Interview Summary Paper No(s)/Mail D		
3) Information Disclosure Statement(s) (PTO-14 Paper No(s)/Mail Date	49 or PTO/SB/08)	6) Other:	atom Apphoason (i 10-102)	

DETAILED ACTION

This Office Action is in response to Applicant's Amendment dated 11/23/2005.

Election/Restrictions

1. This application contains claims 1-14 drawn to an invention nonelected with traverse in the reply to elections/restriction dated 06/13/2005. A complete reply to the final rejection must include cancellation of nonelected claims or other appropriate action (37 CFR 1.144) See MPEP § 821.01.

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

- 2. Claims 15-21 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- ▶ With respect to claim 15,

lines 5-6, the limitation "depositing <u>a layer of material with a planar surface</u> substantially the same as the conductive layer over the conductive layer" renders the claim indefinite. It is not clear which characteristics of the layer of material is considered as substantially the same as the conductive layer – the material of the layer of material <u>OR</u> the planar surface of the layer of material? It is not clear that:

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- "a layer of material with a planar surface substantially the same as the conductive layer" means that "a layer of material having a planar surface wherein the planar surface of the layer of material being substantially the same as a planar surface of the conductive layer"; OR

- "a layer of material with a planar surface substantially the same as the conductive layer" means that "a layer of material having a planar surface wherein material of the layer of material being substantially the same as a material of the conductive layer".

For the purpose of examination, Examiner considers that the step of "depositing a layer of material with a planar surface substantially the same as the conductive layer over the conductive layer" means that "depositing a layer of material with a planar surface over the conductive layer, wherein material of the layer of material being substantially the same as a material of the conductive layer".

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

1. Claims 15-20 are rejected under 35 U.S.C. 102(e) as being anticipated by Hsu et al [US 2004/0067640] previously applied.

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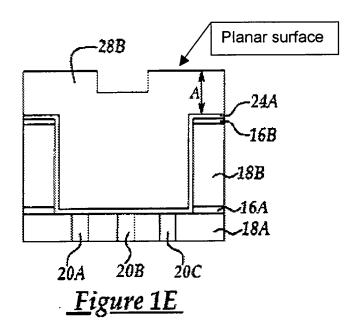
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▶ With respect to claim 15, Hsu et al (figs 1's-2, text [0001]-[0033]) discloses the claimed CMP rework method comprising steps of:

providing a semiconductor substrate which has a patterned dielectric layer (16A/18B/16B, fig. 1C, text [0023]-[0027]), a barrier layer (24A) over the patterned dielectric layer, and a conductive layer (28A) over the barrier layer;

performing a first CMP process to remove part of the conductive layer (figs. 1C-1D, text [0028]);

depositing a layer of material (28B, fig 1E, text [0030]) with a planar surface over the conductive layer (see figure 1E below), wherein material of the layer of material (28B) being substantially the same as a material of the conductive layer (28A); and performing a second CMP process to expose the patterned dielectric layer (fig 1E-1F, text [0031]).



▶ With respect to claim 16, Hsu et al (text [0023]-[0027]) discloses the conductive

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layer comprises copper or copper alloy.

▶ With respect to claim 17, Hsu et al (text [0023]-[0027]) discloses the dielectric layer (16A/18B/16B) comprises silicon dioxide, silicon nitride, phosphosilicate glass, borophosphosilicate glass, or fluorosilicate glass.

- ► With respect to claim 18, Hsu et al (text [0023]-[0027]) discloses the barrier layer (24A) comprises Ta, Ti, TaN, TiN, or WN.
- ▶ With respect to claim 19, Hsu et al (text [0023]-[0027]) discloses the deposition of copper or copper alloy is performed using electroplating, CVD, or PVD.
- ▶ With respect to claim 20, Hsu et al (fig 1E) discloses the top surface of the layer (28B) deposited in the step of depositing a layer of material substantially the same as the conductive layer over the conductive layer higher than the barrier layer (24A).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claim 21 is rejected under 35 U.S.C. 103(a) as being unpatentable over Hsu et al [US 2004/0067640] in view of Gotkis et al [US 2004/0058620].

Hsu et al substantially discloses the claimed method except teaching the semiconductor substrate is reported as an abnormally polished wafer by a CMP machine at a predetermined CMP endpoint after performing said first CMP process to remove said part of said conductive layer.

However, Gotkis et al (fig 4, text [0001]-[0095]) discloses using the CMP machine for checking and reporting the semiconductor substrate if the semiconductor substrate is the abnormally polished wafer at the predetermined CMP endpoint after performing a CMP process to remove the part of the conductive layer and subjecting the abnormally polished wafer to rework process.

Therefore, at the time of invention, it would have been obvious for those skilled in the art to modify the process of Hsu et al by using the CMP machine for reporting the semiconductor wafer as being claimed, per taught by Gotkis et al, to provide a better controlled and convenient CMP rework process with increased efficiency such as time saving of handling processed wafer (see Gotkis et al, text [0023] and [0042] specifically).

Response to Arguments

3. Applicant's arguments filed 11/23/20005 have been fully considered but they are not persuasive.

Applicant argues that the second copper layer 28B of Hsu is not planar. The argument is not persuasive because Hsu clearly discloses the second copper layer 28B having a planar surface (see fig. 1E above). Furthermore, Applicant does not claim that the entire upper surface of the layer of material is planar. Therefore, Hsu still meets and anticipates the claimed language of Applicant's invention.

Conclusion

4. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanhha Pham whose telephone number is (571) 272-1696. The examiner can normally be reached on Monday and Thursday 9:00AM - 9:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

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you have questions on access to the Private PAIR system, contact the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

Thanhha Pham Patent Examiner

Patent Examining Group 2800